

## **CLAIMS:**

What is claimed is:

1. A method comprising:  
patterning a signal line from a metal material as a terminal conductive layer of an integrated circuit die;  
patterning a first protective structure to surround the signal line; and  
patterning a second protective structure to surround the first protective structure.
2. The method of claim 1, further comprising:  
patterning the first protective structure as a continuous structure to enclose the signal line.
3. The method of claim 1, further comprising:  
patterning the first and second protective structures to one of a low rail supply line and a high rail supply line.
4. A method comprising:  
forming a first interconnection metallization layer on a substrate;  
forming a second interconnection metallization layer on the first interconnection metallization layer;  
forming at least one signal line coupled to the first interconnection metallization layer in the second interconnection metallization;  
forming at least one protective structure that surrounds the at least one signal line in the second interconnection metallization layer.
5. The method of claim 4, wherein the forming at least one protective structure that surrounds the at least one signal line comprises using a continuous loop-like shape protective structure to enclose the signal line.
6. The method of claim 4, further comprising coupling the at least one protective structure to a low rail supply voltage.

7. The method of claim 4, further comprising coupling the at least one protective structure to a high rail supply voltage.
8. The method of claim 4, wherein the at least one protective structure is spaced from the signal line at approximately 2 microns.
9. The method of claim 4, wherein the first interconnection metallization layer has a first volume and the second interconnection metallization layer has a second volume greater than the first volume.
10. The method of claim 4, wherein the forming at least one protective structure comprises forming a plurality of protective structures (PSi) for  $i = 1 \dots N$ , a first protective structure PS1 surrounding the signal line, each protective structure PSi surrounding a previous protective structure PSi-1.